Abstracts

GaAs Schottky Barrier Diodes for THz Applications

T.W. Crowe, W.C.B. Peatman, P.A.D. Wood and X. Liu. "GaAs Schottky Barrier Diodes for THz Applications." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 1141-1144.

GaAs Schottky barrier diodes are used as nonlinear elements for a variety of scientific applications at frequencies as high as 3 THz. The factors that limit the high frequency performance of these diodes are reviewed and the design process is discussed. Recent results with ultra-small Schottky anodes are presented and conclusions are draw about the future of Schottky diodes at THz frequencies.

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